

Supplementary Information: Tuning the hydrogen evolution activity of MS₂ (M = Mo or Nb) monolayers by strain engineering

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1. Data for ΔG calculations

Table S1. Total energies for a isolated H atom $E(\text{H})$, a H atom in gas molecular state ($E(\text{H}_2)/2$), and their difference ΔE_{cp} . $E_{\text{ZPE}}(\text{gas})$ and $E_{\text{ZPE}}(\text{ads})$ are the zero point energies of a H atom in gas molecular state and adsorbed state, respectively. The calculated $E_{\text{ZPE}}(\text{gas})$ is 0.137 eV, in good agreement with the previous value of 0.135 eV.¹ $T\Delta S_{\text{H}}$ is obtained from the literature.¹

	$E(\text{H})$	$E(\text{H}_2)/2$	ΔE_{cp}	$E_{\text{ZPE}}(\text{gas})$	$E_{\text{ZPE}}(\text{ads})$	$T\Delta S_{\text{H}}$	$\Delta E_{\text{ZPE}} - T\Delta S_{\text{H}}$
1H-MoS ₂					0.194		0.262
1T-MoS ₂	-0.000488	-3.380413	3.380	0.137	0.228	-0.205	0.296
1H-NbS ₂					0.229		0.297
1T-NbS ₂					0.229		0.297

All the total energies calculated by VASP are with respect to the atomic energies in reference configuration (*i.e.* the configuration for which the pseudopotential is generated). Consequently, $E(\text{H})$ should be as small as possible. The small value of -0.000488 eV for $E(\text{H})$ indicates the high accuracy of the PAW potential. In addition, it is seen that $E_{\text{ZPE}}(\text{ads})$ is weakly dependent on different materials.

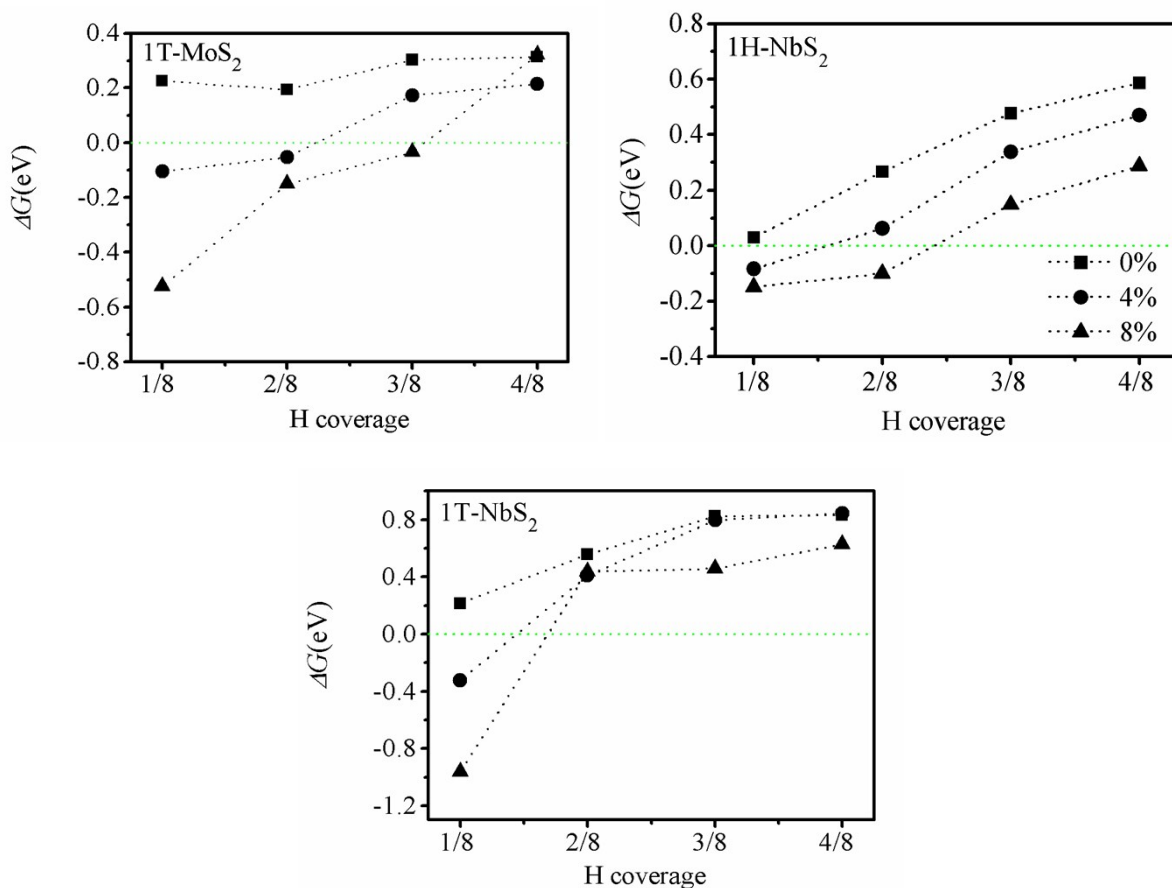


Fig. S1 (color online) H coverage dependent differential ΔG for monolayer 1T-MoS₂, 1H-NbS₂ and 1T-NbS₂ for biaxial tensile strain of 0% (squares), 4% (circles) and 8% (triangles). Only H coverage from 1/8 to 4/8 is considered.

Generally, ΔG increases with increasing H coverage for all the monolayer disulfides. For a given disulfide, the evolution of ΔG with H coverage, as indicated by dotted lines, may cross the green horizontal lines ($\Delta G = 0$). The coverage corresponding to the crossover is selected to be the max coverage of H (MCH) defined in the text. This may lead to an average error of *ca.* $\pm 1/16$ for the MCH.

REFERENCES

1. J. K. Nørskov, T. Bligaard, A. Logadottir, J. R. Kitchin, J. G. Chen, S. Pandelov and U. Stimming, *J. Electrochem. Soc.*, 2005, **152**, J23-J26.